Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims

Claim 1 (Currently amended)

A method for forming an adhesion between dielectric layers, the method comprising:

providing a first dielectric layer; and

in-situ forming a second dielectric layer having a first portion on said first dielectric layer and a second portion on said first portion, wherein said first portion has a first dielectric constant higher than said second portion has and said first portion comprises carbon.

Claim 2 (Original)

The method according to claim 1, wherein said first dielectric layer has a second dielectric constant which is higher than said second portion.

Claim 3 (Original)

The method according to claim 1, wherein the in-situ forming step having at least a process condition for forming said first portion and said second portion.

Claim 4 (Original)

The method according to claim 3, wherein the in-situ forming step having said process condition comprises:

executing a chemical vapor deposition having a first bias; and

executing said chemical vapor deposition having a second bias, wherein said first bias is higher than said second bias.

Claim 5 (Original)

The method according to claim 3, wherein the in-situ forming step having said process condition comprises:

executing a chemical vapor deposition having a first HFRF for forming said first portion; and

executing said chemical vapor deposition having a second HFRF, wherein said first HFRF is higher than said second HFRF.

Claim 6 (Original)

The method according to claim 3, wherein the in-situ forming step having said process condition comprises:

executing a chemical vapor deposition having a first precursor for forming said first portion; and

executing said chemical vapor deposition having a second precursor, wherein the amount of said first precursor is less than the amount of said second precursor.

Claim 7 (Original)

The method according to claim 1, wherein the in-situ forming step comprises plasma enhanced chemical vapor deposition (PECVD).

Claim 8 (Currently amended)

A method for forming an adhesion between dielectric layers, the method comprising:

providing a first dielectric layer; and

in-situ forming a second dielectric layer having a first portion on said first dielectric layer and a second portion on said first portion, wherein said first portion has a hardness higher than said second portion has and said first portion comprises carbon.

Claim 9 (Original)

The method according to claim 8, wherein said first dielectric layer has a dielectric constant which is higher than said second dielectric layer.

Claim 10 (Original)

The method according to claim 8, wherein the in-situ forming step at least comprises:

executing a chemical vapor deposition having a first bias for forming said first portion; and

executing said chemical vapor deposition having a second bias for forming said second portion, wherein said first bias is higher than said second bias.

Claim 11 (Currently amended)

The method according to claim 8, wherein the in-situ forming step at least comprises:

executing a chemical vapor deposition having a first HFRF for forming said first portion; and

executing said chemical vapor deposition having a second HFRF for forming said second portion, wherein said first HFRF~~bias~~ is higher than said second HFRF~~bias~~.

Claim 12 (Currently amended)

The method according to claim 8, wherein the in-situ forming step at least comprises:

executing a chemical vapor deposition having a first precursor for forming said first portion; and

executing said chemical vapor deposition having a second precursor for forming said second portion, wherein the amount of said first precursor~~bias~~ is higher than said second precursor~~bias~~.

Claim 13 (Currently amended)

The method according to claim [[1]] 8, wherein the in-situ forming step comprises:

executing a chemical vapor deposition having a first process condition; and

executing said chemical vapor deposition having a second process condition, wherein said second process condition forming said second

portion having a dielectric constant smaller than said first process condition forming said first portion.

Claim 14 (Original)

The method according to claim 13, wherein said executing said chemical vapor deposition is plasma enhanced chemical vapor deposition (PECVD).

Claim 15 (Currently amended)

An structure of enhanced-inter-adhesion dielectric layers, the structure comprising:

a first dielectric layer; and

a second dielectric layer having a first portion on said first dielectric layer and a second portion on said first portion, wherein said first portion has a first dielectric constant around 2.8 to 3.5 higher than said second portion and said first portion comprises carbon.

Claim 16 (Original)

The structure according to claim 15, wherein said first dielectric layer is silicon nitride (SiN).

Claim 17 (Original)

The structure according to claim 15, wherein said first dielectric layer is silicon carbide (SiC).

Claim 18 (Original)

The structure according to claim 15, wherein said second portion has a second dielectric constant around 1.1 to 3.